

# SANYO Semiconductors DATA SHEET

SBS817 — Low VF Schottky Barrier Diode 15V, 2.0A Rectifier

## **Applications**

· High frequency rectification (switching regulators, converters, choppers).

#### **Features**

- · Small switching noise.
- · Low forward voltage- (IF=2.0A, VF max=0.46V)
- · Ultrasmall package permitting applied sets to be small and slim (Mounting height 0.75mm).

#### **Specifications**

Absolute Maximum Ratings at Ta=25°C (Value per element)

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		15	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		15	V
Average Output Current	IO		2.0	Α
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	20	А
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Marking: SB

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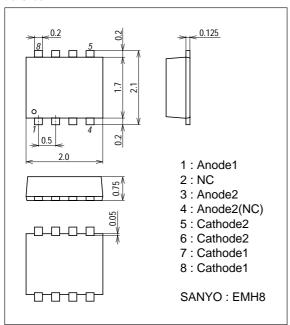
<sup>\*:</sup> The absolute maximum ratings and electrical characteristics refer to those between Terminal 1 and Terminal 7 (or 8), and between Terminal 3 and Terminal 5 (or 6).

#### **Electrical Characteristics** at Ta=25°C (Value per element)

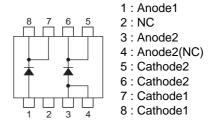
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Reverse Voltage	٧R	IR=1mA	15			V
Forward Voltage	V <sub>F</sub> 1	IF=1.0A		0.33	0.39	V
	V <sub>F</sub> 2	I <sub>F</sub> =2.0A		0.39	0.46	V
Reverse Current	IR	V <sub>R</sub> =7.5V			300	μΑ
Interterminal Capacitance	С	V <sub>R</sub> =10V, f=1MHz		35		pF
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =I <sub>R</sub> =100mA, See specified Test Circuit.			10	ns
Thermal Resistance	Rth(j-a)	When mounted on ceramic substrate (900mm²X0.8mm)		65		°C/W

### **Package Dimensions**

unit : mm (typ) 7045-004



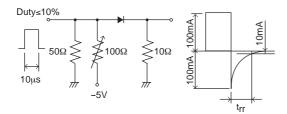
#### **Electrical Connection**

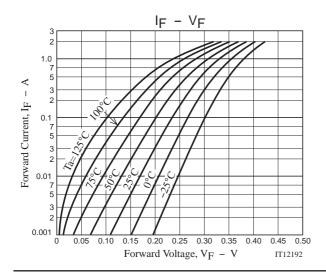


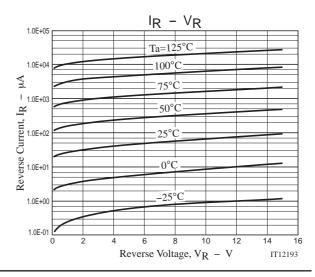
Top view

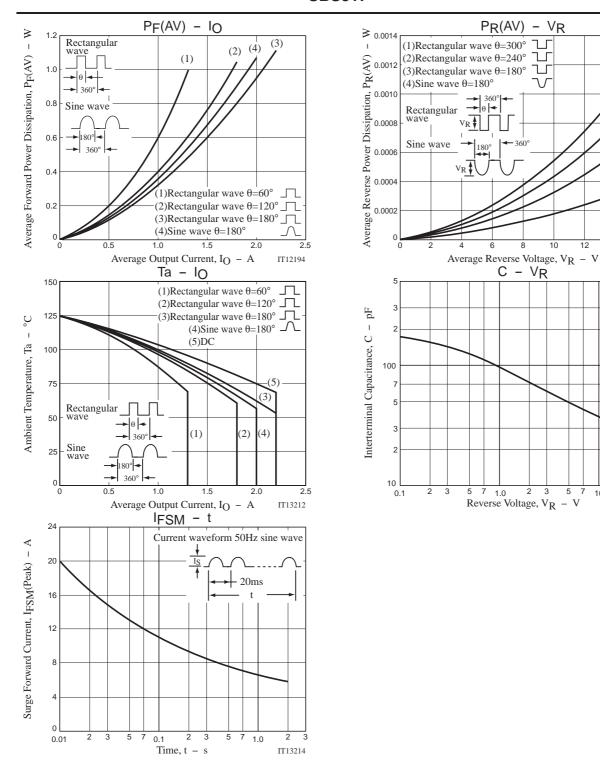
\*: Terminal 4 is used for the purposes such as test. Although it is connected to Anode 2, please handle it as NC Terminal

# trr Test Circuit









(1)

(2)

(3)

f=1MHz

IT13213

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